

General Description

The MY015CDC is the highest performance trench N-ch MOSFETs with extreme high ell density, which provide excellent $R_{DS(ON)}$ and gate charge for most of the small power switching and load switch applications.

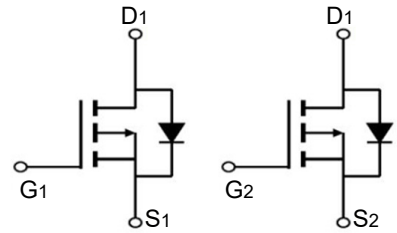
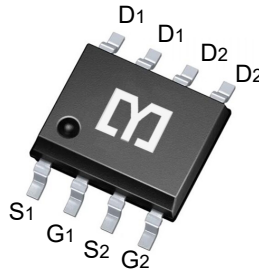


Features

V_{DSS}	-30	V
I_D	-30	A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	<15	m Ω
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	<20	m Ω

Application

- Battery protection
- Load switch
- Uninterruptible power supply



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MY015CDC	SOP-8	015DDC	3000

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_{D@T_A=25^{\circ}\text{C}}$	Continuous Drain Current, V_{GS} @ -10V ¹	-30	A
$I_{D@T_A=70^{\circ}\text{C}}$	Continuous Drain Current, V_{GS} @ -10V ¹	-18	A
I_{DM}	Pulsed Drain Current ²	-50	A
EAS	Single Pulse Avalanche Energy ³	72.2	mJ
I_{AS}	Avalanche Current	-38	A
$P_{D@T_A=25^{\circ}\text{C}}$	Total Power Dissipation ⁴	3.1	W
$P_{D@T_A=70^{\circ}\text{C}}$	Total Power Dissipation ⁴	2	W
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	75	$^{\circ}\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Ambient ¹ ($t_{\leq 10s}$)	40	$^{\circ}\text{C/W}$
	Thermal Resistance Junction-Case ¹	24	$^{\circ}\text{C/W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=-1mA$	---	-0.022	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V, I_D=-6A$	---	11	15	$m\Omega$
		$V_{GS}=-4.5V, I_D=-4A$	---	15	20	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.0	---	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.6	---	$mV/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-24V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	-1	μA
		$V_{DS}=-24V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-5V, I_D=-6A$	---	17	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	---	13	---	Ω
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-15V, V_{GS}=-4.5V, I_D=-6A$	---	12.6	---	nC
Q_{gs}	Gate-Source Charge		---	4.8	---	
Q_{gd}	Gate-Drain Charge		---	4.8	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-15V, V_{GS}=-10V, R_G=3.3\Omega, I_D=-6A$	---	4.6	---	ns
T_r	Rise Time		---	14.8	---	
$T_{d(off)}$	Turn-Off Delay Time		---	41	---	
T_f	Fall Time		---	19.6	---	
C_{iss}	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, f=1MHz$	---	1600	---	pF
C_{oss}	Output Capacitance		---	390	---	
C_{rss}	Reverse Transfer Capacitance		---	175	---	
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	-9.5	A
I_{SM}	Pulsed Source Current ^{2,5}		---	---	-50	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1.2	V
t_{rr}	Reverse Recovery Time	$I_F=-6A, dI/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	16.3	---	nS
Q_{rr}	Reverse Recovery Charge	$T_J=25^\circ\text{C}$	---	5.9	---	nC

Note :

1.The data tested by surface mounted on a 1 inch ²FR-4 board with 20Z copper.2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$ 3.The EAS data shows Max. rating . The test condition is $V_{DD}=-25V, V_{GS}=-10V, L=0.1mH, I^{AS}=-38A$ 4.The power dissipation is limited by 150°C junction temperature5 .The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Electrical and Thermal Characteristics

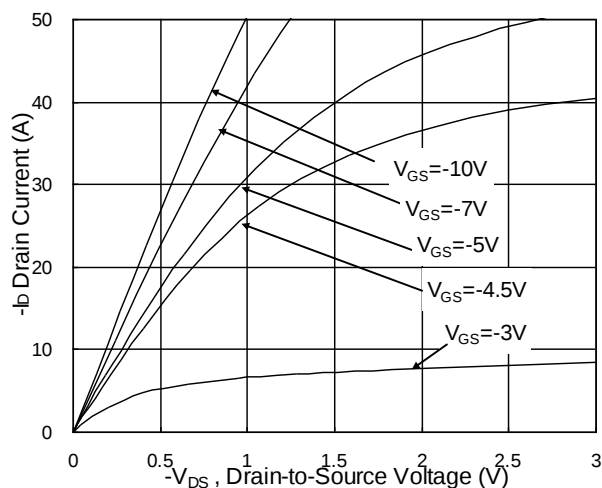


Fig.1 Typical Output Characteristics

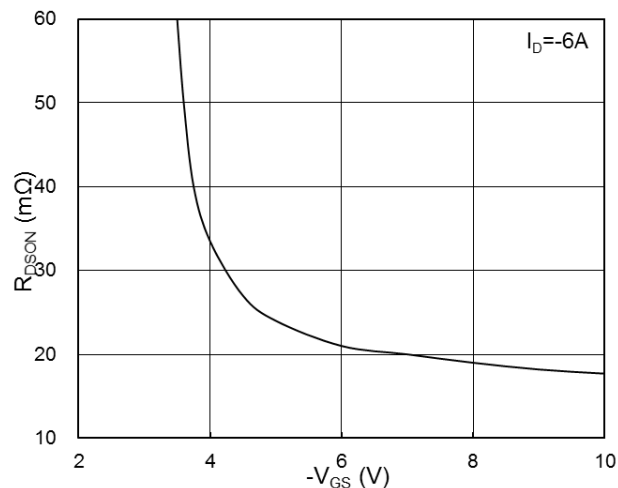


Fig.2 On-Resistance v.s Gate-Source

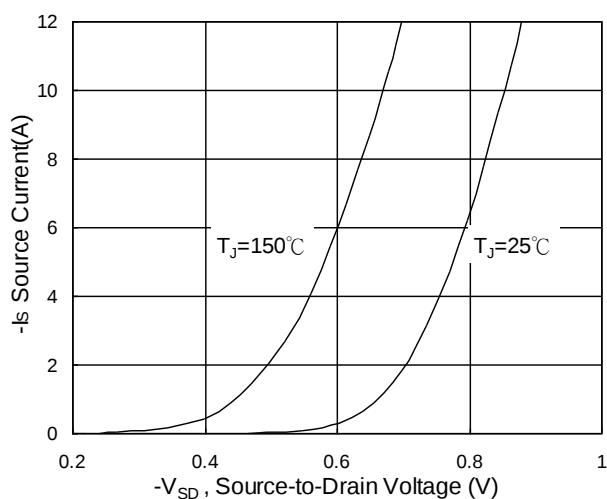


Fig.3 Forward Characteristics of Reverse

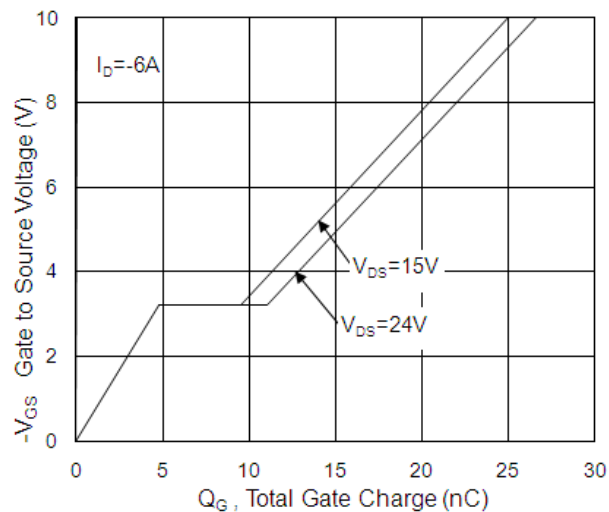


Fig.4 Gate-Charge Characteristics

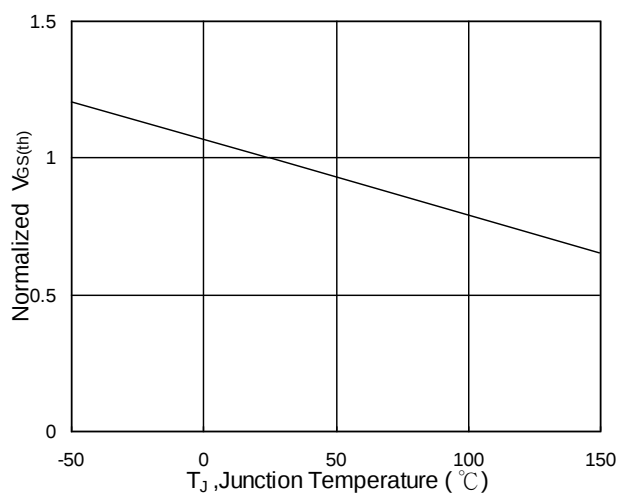


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

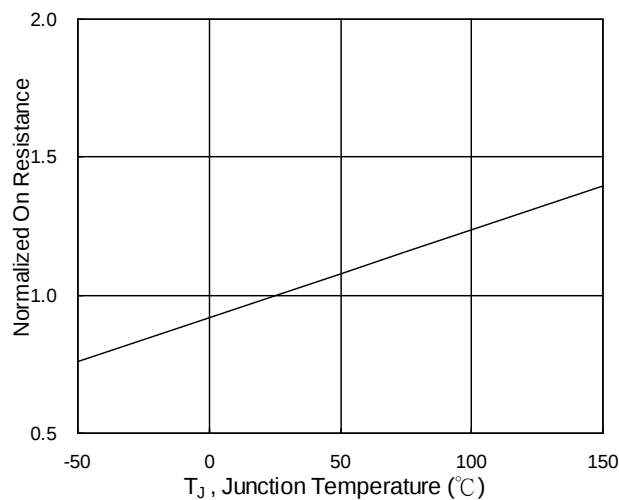


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

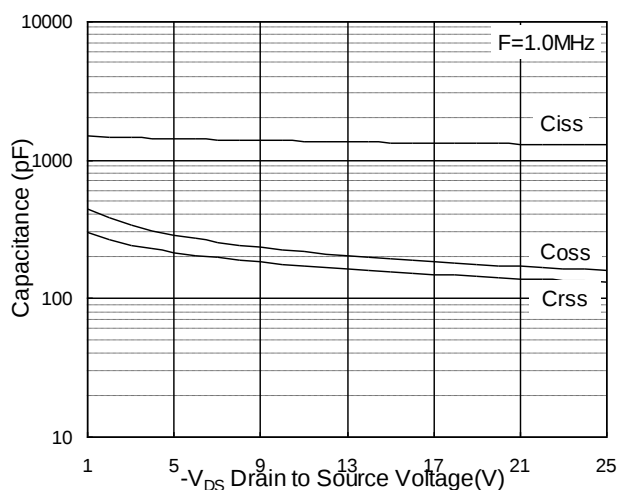


Fig.7 Capacitance

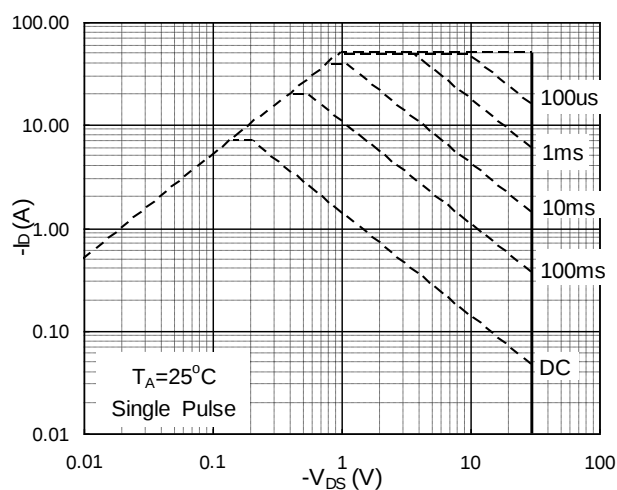


Fig.8 Safe Operating Area

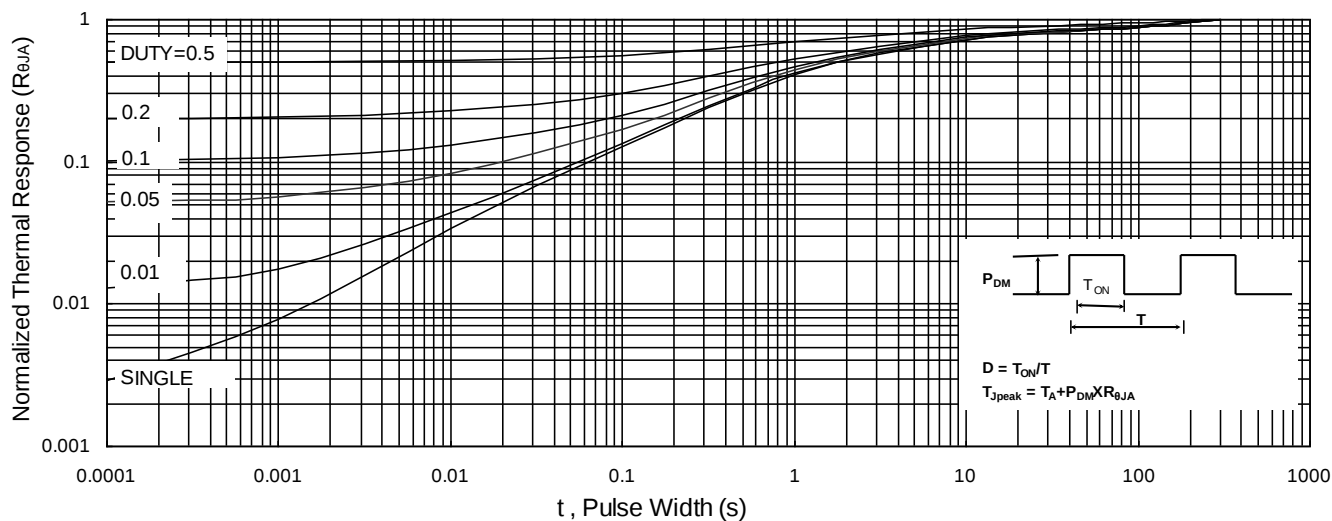


Fig.9 Normalized Maximum Transient Thermal Impedance

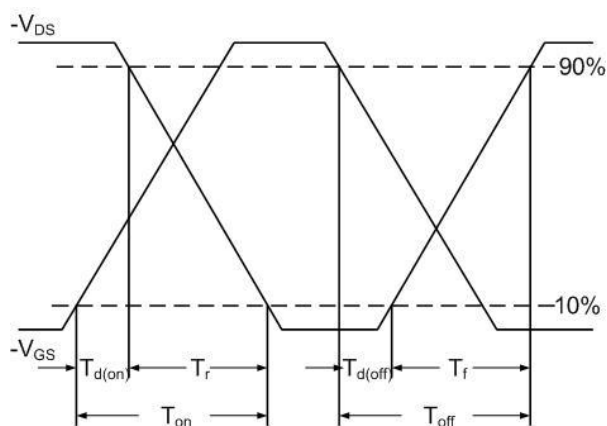


Fig.10 Switching Time Waveform

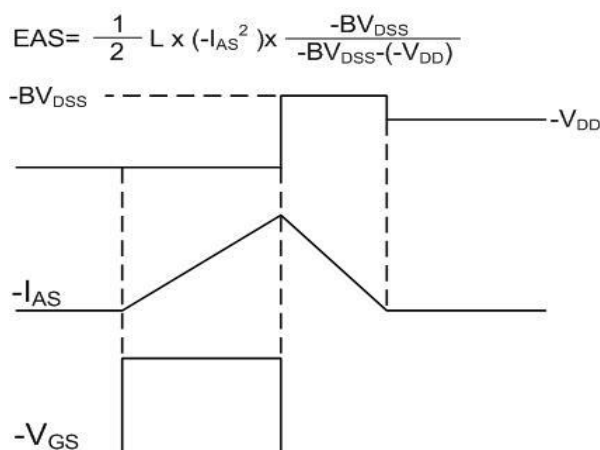
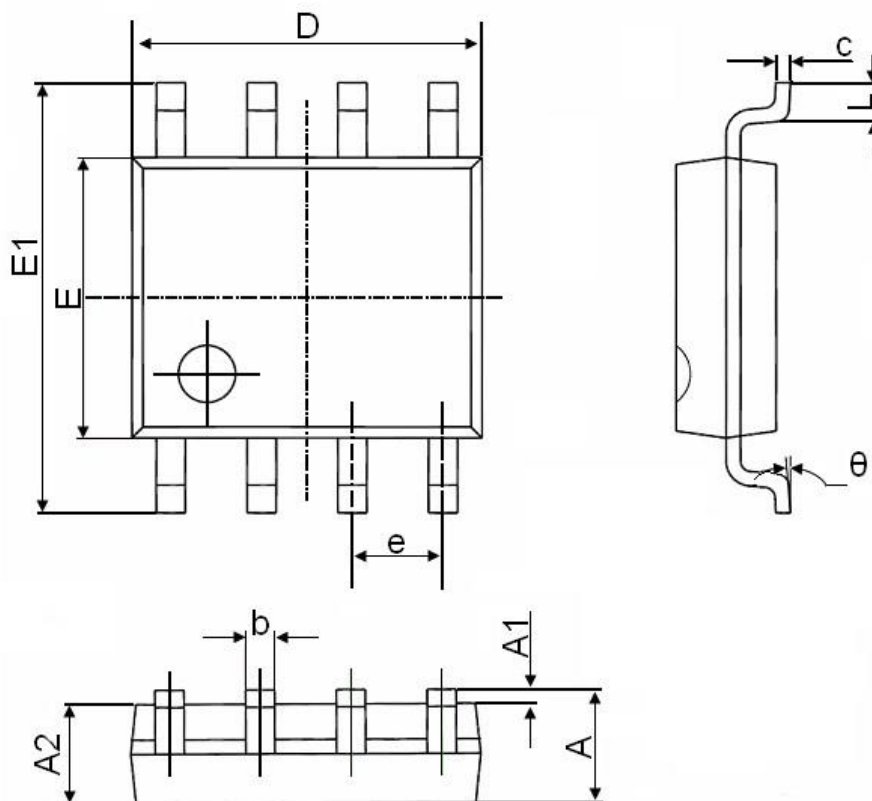


Fig.11 Unclamped Inductive Switching Waveform

Package Mechanical Data-SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050